E.) Crattice Semiconductor Corporation - <u>LCMXO3LF-1300E-6MG121I Datasheet</u>



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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	160
Number of Logic Elements/Cells	1280
Total RAM Bits	65536
Number of I/O	100
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	121-VFBGA, CSPBGA
Supplier Device Package	121-CSFBGA (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3lf-1300e-6mg121i

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Table 1-1. MachXO3L/LF Family Selection Guide

Features		MachXO3L-640/ MachXO3LF-640	MachXO3L-1300/ MachXO3LF-1300	MachXO3L-2100/ MachXO3LF-2100	MachXO3L-4300/ MachXO3LF-4300	MachXO3L-6900/ MachXO3LF-6900	MachXO3L-9400/ MachXO3LF-9400
LUTs		640	1300	2100	4300	6900	9400
Distributed R/	AM (kbits)	5	10	16	34	54	73
EBR SRAM (I	kbits)	64	64	74	92	240	432
Number of PL	Ls	1	1	1	2	2	2
Hardened	l ² C	2	2	2	2	2	2
Functions:	SPI	1	1	1	1	1	1
	Timer/Counter	1	1	1	1	1	1
	Oscillator	1	1	1	1	1	1
MIPI D-PHY S	Support	Yes	Yes	Yes	Yes	Yes	Yes
Multi Time Pr NVCM	ogrammable	MachXO3L-640	MachXO3L-1300	MachXO3L-2100	MachXO3L-4300	MachXO3L-6900	MachXO3L-9400
Programmable Flash		MachXO3LF-640	MachXO3LF-1300	MachXO3LF-2100	MachXO3LF-4300	MachXO3LF-6900	MachXO3LF-9400
Packages				ΙΟ			
36-ball WLCS (2.5 mm x 2.5	6P ¹ 6 mm, 0.4 mm)		28				
49-ball WLCS (3.2 mm x 3.2	P ¹ mm, 0.4 mm)			38			
81-ball WLCSP ¹ (3.8 mm x 3.8 mm, 0.4 mm)					63		
121-ball csfBGA ¹ (6 mm x 6 mm, 0.5 mm)		100	100	100	100		
256-ball csfB (9 mm x 9 mn	GA ¹ n, 0.5 mm)		206	206	206	206	206
324-ball csfB (10 mm x 10	GA ¹ mm, 0.5 mm)		2	268	268	281	
256-ball caBC (14 mm x 14 i	àA² mm, 0.8 mm)		206	206	206	206	206
324-ball caBC (15 mm x 15 i	àA² mm, 0.8 mm)			279	279	279	
400-ball caB0 (17 mm x 17 i	àA² mm, 0.8 mm)				335	335	335
484-ball caBC (19 mm x 19	3A² mm, 0.8 mm)						384

1. Package is only available for E=1.2 V devices.

2. Package is only available for C=2.5 V/3.3 V devices.

Introduction

MachXO3[™] device family is an Ultra-Low Density family that supports the most advanced programmable bridging and IO expansion. It has the breakthrough IO density and the lowest cost per IO. The device IO features have the integrated support for latest industry standard IO.

The MachXO3L/LF family of low power, instant-on, non-volatile PLDs has five devices with densities ranging from 640 to 9400 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic these devices feature Embedded Block RAM (EBR), Distributed RAM, Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support, advanced configuration support including dual-boot capability and hardened versions of commonly used functions such as SPI controller, I²C controller and timer/counter. MachXO3LF devices also support User Flash Memory (UFM). These features allow these devices to be used in low cost, high volume consumer and system applications.

The MachXO3L/LF devices are designed on a 65nm non-volatile low power process. The device architecture has several features such as programmable low swing differential I/Os and the ability to turn off I/O banks, on-chip PLLs







 MachXO3L/LF-1300, MachXO3L/LF-2100, MachXO3L/LF-6900 and MachXO3L/LF-9400 are similar to MachXO3L/LF-4300. MachXO3L/LF-1300 has a lower LUT count, one PLL, and seven EBR blocks. MachXO3L/LF-2100 has a lower LUT count, one PLL, and eight EBR blocks. MachXO3L/LF-6900 has a higher LUT count, two PLLs, and 26 EBR blocks. MachXO3L/LF-9400 has a higher LUT count, two PLLs, and 48 EBR blocks.

• MachXO3L devices have NVCM, MachXO3LF devices have Flash.

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO3L/LF family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag "hard" control logic to minimize LUT usage.

The MachXO3L/LF registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO3L/LF architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. These blocks are located at the ends of the on-chip NVCM/Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO3L/LF devices provide commonly used hardened functions such as SPI controller, I²C controller and timer/ counter.

MachXO3LF devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I²C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO3L/LF devices are available for operation from 3.3 V, 2.5 V and 1.2 V power sup-plies, providing easy integration into the overall system.



ROM Mode

ROM mode uses the LUT logic; hence, slices 0-3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information on the RAM and ROM modes, please refer to TN1290, Memory Usage Guide for MachXO3 Devices.

Routing

There are many resources provided in the MachXO3L/LF devices to route signals individually or as buses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The inter-PFU connections are made with three different types of routing resources: x1 (spans two PFUs), x2 (spans three PFUs) and x6 (spans seven PFUs). The x1, x2, and x6 connections provide fast and efficient connections in the horizontal and vertical directions.

The design tools take the output of the synthesis tool and places and routes the design. Generally, the place and route tool is completely automatic, although an interactive routing editor is available to optimize the design.

Clock/Control Distribution Network

Each MachXO3L/LF device has eight clock inputs (PCLK [T, C] [Banknum]_[2..0]) – three pins on the left side, two pins each on the bottom and top sides and one pin on the right side. These clock inputs drive the clock nets. These eight inputs can be differential or single-ended and may be used as general purpose I/O if they are not used to drive the clock nets. When using a single ended clock input, only the PCLKT input can drive the clock tree directly.

The MachXO3L/LF architecture has three types of clocking resources: edge clocks, primary clocks and secondary high fanout nets. MachXO3L/LF devices have two edge clocks each on the top and bottom edges. Edge clocks are used to clock I/O registers and have low injection time and skew. Edge clock inputs are from PLL outputs, primary clock pads, edge clock bridge outputs and CIB sources.

The eight primary clock lines in the primary clock network drive throughout the entire device and can provide clocks for all resources within the device including PFUs, EBRs and PICs. In addition to the primary clock signals, MachXO3L/LF devices also have eight secondary high fanout signals which can be used for global control signals, such as clock enables, synchronous or asynchronous clears, presets, output enables, etc. Internal logic can drive the global clock network for internally-generated global clocks and control signals.

The maximum frequency for the primary clock network is shown in the MachXO3L/LF External Switching Characteristics table.

Primary clock signals for the MachXO3L/LF-1300 and larger devices are generated from eight 27:1 muxes The available clock sources include eight I/O sources, 11 routing inputs, eight clock divider inputs and up to eight sys-CLOCK PLL outputs.



If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1290, Memory Usage Guide for MachXO3 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO3L/LF devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO3L/LF devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

All PIO pairs can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these devices have on-chip differential termination and also provide PCI support.



Input Gearbox

Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Table 2-9. Input Gearbox Signal List

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDRX4(1:8): Q[7:0] GDDRX2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDRX2(1:4)(IOL-C): Q0, Q1, Q2, Q3

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-13 shows a block diagram of the input gearbox.



Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDRX4 (8:1) gearbox or as two ODDRX2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDRX4(8:1): D[7:0]		
GDDRX2(4:1)(IOL-A): D[3:0]		
GDDRX2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-14 shows the output gearbox block diagram.



Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, MachXO3 sysIO Usage Guide.

Table 2-11. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	3.3 V	2.5 V	1.8 V	1.5 V	1.2 V
Single-Ended Interfaces					
LVTTL	Yes				
LVCMOS33	Yes				
LVCMOS25		Yes			
LVCMOS18			Yes		
LVCMOS15				Yes	
LVCMOS12					Yes
PCI	Yes				
Differential Interfaces					
LVDS	Yes	Yes			
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes			
MIPI ¹	Yes	Yes			
LVTTLD	Yes				
LVCMOS33D	Yes				
LVCMOS25D		Yes			
LVCMOS18D			Yes		

1. These interfaces can be emulated with external resistors in all devices.



Figure 2-15. MachXO3L/LF-1300 in 256 Ball Packages, MachXO3L/LF-2100, MachXO3L/LF-4300, MachXO3L/LF-6900 and MachXO3L/LF-9400 Banks



Figure 2-16. MachXO3L/LF-640 and MachXO3L/LF-1300 Banks





Table 2-17. MachXO3L/LF Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Differential I/O buffers (used to implement standards such as LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1289, Power Estimation and Management for MachXO3 Devices.

Power On Reset

MachXO3L/LF devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO} (controls configuration) voltage levels. It then triggers download from the on-chip configuration NVCM/Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For "E" devices without voltage regulators, V_{CCINT} is the same as the V_{CC} supply voltage. For "C" devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as NVCM/Flash Download Time ($t_{REFRESH}$) in the DC and Switching Characteristics section of this data sheet. Before and during configuration. Note that for "C" devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once an "E" device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a mini-mal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.



Security and One-Time Programmable Mode (OTP)

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO3L/LF devices contain security bits that, when set, prevent the readback of the SRAM configuration and NVCM/Flash spaces. The device can be in one of two modes:

- 1. Unlocked Readback of the SRAM configuration and NVCM/Flash spaces is allowed.
- 2. Permanently Locked The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the NVCM/Flash and SRAM OTP portions of the device. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Password

The MachXO3LF supports a password-based security access feature also known as Flash Protect Key. Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. The Flash Protect Key feature provides a method of controlling access to the Configuration and Programming modes of the device. When enabled, the Configuration and Programming edit mode operations (including Write, Verify and Erase operations) are allowed only when coupled with a Flash Protect Key which matches that expected by the device. Without a valid Flash Protect Key, the user can perform only rudimentary non-configuration operations such as Read Device ID. For more details, refer to TN1313, Using Password Security with MachXO3 Devices.

Dual Boot

MachXO3L/LF devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the external SPI Flash. The golden image MUST reside in an on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Soft Error Detection

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1292, MachXO3 Soft Error Detection Usage Guide.

Soft Error Correction

The MachXO3LF device supports Soft Error Correction (SEC). Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. When BACKGROUND_RECONFIG is enabled using the Lattice Diamond Software in a design, asserting the PROGRAMN pin or issuing the REFRESH sysConfig command refreshes the SRAM array from configuration memory. Only the detected error bit is corrected. No other SRAM cells are changed, allowing the user design to function uninterrupted.

During the project design phase, if the overall system cannot guarantee containment of the error or its subsequent effects on downstream data or control paths, Lattice recommends using SED only. The MachXO3 can be then be soft-reset by asserting PROGRAMN or issuing the Refresh command over a sysConfig port in response to SED. Soft-reset additionally erases the SRAM array prior to the SRAM refresh, and asserts internal Reset circuitry to guarantee a known state. For more details, refer to TN1292, MachXO3 Soft Error Detection (SED)/Correction (SEC) Usage Guide.



MachXO3 Family Data Sheet DC and Switching Characteristics

February 2017

Advance Data Sheet DS1047

Absolute Maximum Ratings^{1, 2, 3}

	MachXO3L/LF E (1.2 V)	MachXO3L/LF C (2.5 V/3.3 V)
Supply Voltage V _{CC}	\ldots .–0.5 V to 1.32 V \ldots .	–0.5 V to 3.75 V
Output Supply Voltage V _{CCIO}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
I/O Tri-state Voltage Applied ^{4, 5}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Dedicated Input Voltage Applied ⁴	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature (T ₁)	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

5. The dual function I^2C pins SCL and SDA are limited to -0.25 V to 3.75 V or to -0.3 V with a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
Vaa ¹	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
VCC	Core Supply Voltage for 2.5 V/3.3 V Devices	2.375	3.465	V
V _{CCIO} ^{1, 2, 3}	I/O Driver Supply Voltage	1.14	3.465	V
t _{JCOM}	Junction Temperature Commercial Operation	0	85	°C
t _{JIND}	Junction Temperature Industrial Operation	-40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both the same voltage, they must also be the same supply.

2. See recommended voltages by I/O standard in subsequent table.

3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

Power Supply Ramp Rates¹

	iyp.	wax.	Units
t _{RAMP} Power supply ramp rates for all power supplies. 0.01	—	100	V/ms

1. Assumes monotonic ramp rates.

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DC Electrical Characteristics

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
		Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)			+175	μΑ
		Clamp OFF and $V_{IN} = V_{CCIO}$	-10	—	10	μΑ
I _{IL} , I _{IH} ^{1, 4}	Input or I/O Leakage	Clamp OFF and V _{CCIO} - 0.97 V < V _{IN} < V _{CCIO}	-175	_	—	μA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} - 0.97 V	_		10	μΑ
		Clamp OFF and V _{IN} = GND	_		10	μΑ
		Clamp ON and 0 V < V_{IN} < V_{CCIO}			10	μΑ
I _{PU}	I/O Active Pull-up Current	0 < V _{IN} < 0.7 V _{CCIO}	-30		-309	μΑ
I _{PD}	I/O Active Pull-down Current	V _{IL} (MAX) < V _{IN} < V _{CCIO}	30	—	305	μA
I _{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL} (MAX)$	30	—	—	μA
I _{BHHS}	Bus Hold High sustaining current	V _{IN} = 0.7V _{CCIO}	-30	_	_	μΑ
I _{BHLO}	Bus Hold Low Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	_	—	305	μΑ
І _{внно}	Bus Hold High Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	_	_	-309	μΑ
V _{BHT} ³	Bus Hold Trip Points		V _{IL} (MAX)	—	V _{IH} (MIN)	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)$	3	5	9	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)$	3	5.5	7	pf
		V _{CCIO} = 3.3 V, Hysteresis = Large	_	450	—	mV
		V _{CCIO} = 2.5 V, Hysteresis = Large		250	—	mV
		V _{CCIO} = 1.8 V, Hysteresis = Large		125	—	mV
V	Hysteresis for Schmitt	V _{CCIO} = 1.5 V, Hysteresis = Large	_	100	_	mV
VHYST	Trigger Inputs ⁵	V _{CCIO} = 3.3 V, Hysteresis = Small	_	250	_	mV
		V _{CCIO} = 2.5 V, Hysteresis = Small	_	150	_	mV
		V _{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V _{CCIO} = 1.5 V, Hysteresis = Small	_	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. T_A 25 °C, f = 1.0 MHz.

3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.

 When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6mA can occur on the high-tolow transition. For true LVDS output pins in MachXO3L/LF devices, V_{IH} must be less than or equal to V_{CCIO}.

5. With bus keeper circuit turned on. For more details, refer to TN1280, MachXO3 sysIO Usage Guide.



LVDS Emulation

MachXO3L/LF devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.





Note: All resistors are ±1%.

Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Тур.	Units
Z _{OUT}	Output impedance	20	Ohms
R _S	Driver series resistor	158	Ohms
R _P	Driver parallel resistor	140	Ohms
R _T	Receiver termination	100	Ohms
V _{OH}	Output high voltage	1.43	V
V _{OL}	Output low voltage	1.07	V
V _{OD}	Output differential voltage	0.35	V
V _{CM}	Output common mode voltage	1.25	V
Z _{BACK}	Back impedance	100.5	Ohms
I _{DC}	DC output current	6.03	mA



Maximum sysIO Buffer Performance

I/O Standard	Max. Speed	Units
MIPI	450	MHz
LVDS25	400	MHz
LVDS25E	150	MHz
BLVDS25	150	MHz
BLVDS25E	150	MHz
MLVDS25	150	MHz
MLVDS25E	150	MHz
LVPECL33	150	MHz
LVPECL33E	150	MHz
LVTTL33	150	MHz
LVTTL33D	150	MHz
LVCMOS33	150	MHz
LVCMOS33D	150	MHz
LVCMOS25	150	MHz
LVCMOS25D	150	MHz
LVCMOS18	150	MHz
LVCMOS18D	150	MHz
LVCMOS15	150	MHz
LVCMOS15D	150	MHz
LVCMOS12	91	MHz
LVCMOS12D	91	MHz



Figure 3-6. Receiver GDDR71_RX. Waveforms



Figure 3-7. Transmitter GDDR71_TX. Waveforms





NVCM/Flash Download Time^{1, 2}

Symbol	Parameter	Device	Тур.	Units
t _{REFRESH}	POR to Device I/O Active	LCMXO3L/LF-640	1.9	ms
		LCMXO3L/LF-1300	1.9	ms
		LCMXO3L/LF-1300 256-Ball Package	1.4	ms
	LCMXO3L/LF-2100	1.4	ms	
		LCMXO3L/LF-2100 324-Ball Package	2.4	ms
		LCMXO3L/LF-4300	2.4	ms
	LCMXO3L/LF-4300 400-Ball Package	3.8	ms	
	LCMXO3L/LF-6900	3.8	ms	
		LCMXO3L/LF-9400C	5.2	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.

2. The NVCM/Flash download time is measured starting from the maximum voltage of POR trip point.



MachXO3 Family Data Sheet Pinout Information

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Signal Descriptions

Signal Name	I/O	Descriptions	
General Purpose			
		[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top).	
		[Row/Column Number] indicates the PFU row or the column of the device on which the PIO Group exists. When Edge is T (Top) or (Bottom), only need to specify Row Number. When Edge is L (Left) or R (Right), only need to specify Column Number.	
		[A/B/C/D] indicates the PIO within the group to which the pad is connected.	
P[Edge] [Row/Column Number]_[A/B/C/D]	I/O	Some of these user-programmable pins are shared with special function pins. When not used as special function pins, these pins can be programmed as I/Os for user logic.	
		During configuration of the user-programmable I/Os, the user has an option to tri-state the I/Os and enable an internal pull-up, pull-down or buskeeper resistor. This option also applies to unused pins (or those not bonded to a package pin). The default during configuration is for user-programmable I/Os to be tri-stated with an internal pull-down resistor enabled. When the device is erased, I/Os will be tri-stated with an internal pull-down resistor enabled. Some pins, such as PROGRAMN and JTAG pins, default to tri-stated I/Os with pull-up resistors enabled when the device is erased.	
NC	—	No connect.	
GND	—	GND – Ground. Dedicated pins. It is recommended that all GNDs are tied together.	
VCC	_	V_{CC} – The power supply pins for core logic. Dedicated pins. It is recommended that all VCCs are tied to the same supply.	
VCCIOx	_	VCCIO – The power supply pins for I/O Bank x. Dedicated pins. It is recommended that all VCCIOs located in the same bank are tied to the same supply.	
PLL and Clock Functi	ons (Us	ed as user-programmable I/O pins when not used for PLL or clock pins)	
[LOC]_GPLL[T, C]_IN	_	Reference Clock (PLL) input pads: [LOC] indicates location. Valid designations are L (Left PLL) and R (Right PLL). T = true and C = complement.	
[LOC]_GPLL[T, C]_FB	_	Optional Feedback (PLL) input pads: [LOC] indicates location. Valid designations are L (Lef PLL) and R (Right PLL). T = true and C = complement.	
PCLK [n]_[2:0]	—	Primary Clock pads. One to three clock pads per side.	
Test and Programmin	g (Dual f	function pins used for test access port and during sysCONFIG™)	
TMS	I	Test Mode Select input pin, used to control the 1149.1 state machine.	
ТСК	I	Test Clock input pin, used to clock the 1149.1 state machine.	
TDI	I	Test Data input pin, used to load data into the device using an 1149.1 state machine.	
TDO	0	Output pin – Test Data output pin used to shift data out of the device using 1149.1.	
		Optionally controls behavior of TDI, TDO, TMS, TCK. If the device is configured to use the JTAG pins (TDI, TDO, TMS, TCK) as general purpose I/O, then:	
JTAGENB	I	If JTAGENB is low: TDI, TDO, TMS and TCK can function a general purpose I/O.	
		If JTAGENB is high: TDI, TDO, TMS and TCK function as JTAG pins.	
		For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.	

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	MachXO3L/LF-9400C			
	CSFBGA256	CABGA256	CABGA400	CABGA484
General Purpose IO per Bank	•			
Bank 0	50	50	83	95
Bank 1	52	52	84	96
Bank 2	52	52	84	96
Bank 3	16	16	28	36
Bank 4	16	16	24	24
Bank 5	20	20	32	36
Total General Purpose Single Ended IO	206	206	335	383
Differential IO per Bank	·		•	
Bank 0	25	25	42	48
Bank 1	26	26	42	48
Bank 2	26	26	42	48
Bank 3	8	8	14	18
Bank 4	8	8	12	12
Bank 5	10	10	16	18
Total General Purpose Differential IO	103	103	168	192
Dual Function IO	37	37	37	45
Number 7:1 or 8:1 Gearboxes	•			
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	20	20	22	24
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	20	20	22	24
High-speed Differential Outputs	•			
Bank 0	20	20	21	24
VCCIO Pins	·		•	
Bank 0	4	4	5	9
Bank 1	3	4	5	9
Bank 2	4	4	5	9
Bank 3	2	1	2	3
Bank 4	2	2	2	3
Bank 5	2	1	2	3
VCC	8	8	10	12
GND	24	24	33	52
NC	0	1	0	0
Reserved for Configuration	1	1	1	1
Total Count of Bonded Pins	256	256	400	484



MachXO3 Family Data Sheet Supplemental Information

January 2016

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For Further Information

A variety of technical notes for the MachXO3 family are available on the Lattice web site.

- TN1282, MachXO3 sysCLOCK PLL Design and Usage Guide
- TN1281, Implementing High-Speed Interfaces with MachXO3 Devices
- TN1280, MachXO3 sysIO Usage Guide
- TN1279, MachXO3 Programming and Configuration Usage Guide
- TN1074, PCB Layout Recommendations for BGA Packages
- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology
- AN8066, Boundary Scan Testability with Lattice sysIO Capability
- MachXO3 Device Pinout Files
- Thermal Management document
- Lattice design tools

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Date	Version	Section	Change Summary
April 2016	1.6	Introduction	Updated Features section. — Revised logic density range and IO to LUT ratio under Flexible Archi- tecture. — Revised 0.8 mm pitch information under Advanced Packaging. — Added MachXO3L-9400/MachXO3LF-9400 information to Table 1-1, MachXO3L/LF Family Selection Guide.
			Updated Introduction section. — Changed density from 6900 to 9400 LUTs. — Changed caBGA packaging to 19 x 19 mm.
		Architecture	Updated Architecture Overview section. — Changed statement to "All logic density devices in this family" — Updated Figure 2-2 heading and notes.
			Updated sysCLOCK Phase Locked Loops (PLLs) section. — Changed statement to "All MachXO3L/LF devices have one or more sysCLOCK PLL."
			Updated Programmable I/O Cells (PIC) section. — Changed statement to "All PIO pairs can implement differential receivers."
			Updated sysIO Buffer Banks section. Updated Figure 2-5 heading.
			Updated Device Configuration section. Added Password and Soft Error Correction.
		DC and Switching Characteristics	Updated Static Supply Current – C/E Devices section. Added LCMXO3L/ LF-9400C and LCMXO3L/LF-9400E devices.
			Updated Programming and Erase Supply Current – C/E Devices section. — Added LCMXO3L/LF-9400C and LCMXO3L/LF-9400E devices. — Changed LCMXO3L/LF-640E and LCMXO3L/LF-1300E Typ. values.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. Added MachXO3L/LF-9400 devices.
			Updated NVCM/Flash Download Time section. Added LCMXO3L/LF- 9400C device.
		Updated sysCONFIG Port Timing Specifications section. — Added LCMXO3L/LF-9400C device. — Changed t _{INITL} units to from ns to us. — Changed t _{DPPINIT} and t _{DPPDONE} Max. values are per PCN#03A-16.	
	Pinout Information	Updated Pin Information Summary section. Added LCMXO3L/LF-9400C device.	
		Ordering Information	Updated MachXO3 Part Number Description section. — Added 9400 = 9400 LUTs. — Added BG484 package.
			Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.